



Docket No.: IBM/BUR920000119US1
CBLH/21806-00115-US
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Jonathan Chapple-Sokol et al.

Application No.: 09/826,036

Filed: April 4, 2001

For: METHOD OF FORMING REFRACTORY
METAL CONTACT IN AN OPENING, AND
RESULTING STRUCTURE

Group Art Unit: 1753

Examiner: R. McDonald

RECEIVED
MAR 13 2003
GROUP 1700

#7/A
W.M.
3/5/03

AMENDMENT

Commissioner for Patents
Washington, DC 20231

Dear Sir:

In response to the Office Action dated October 25, 2002 (Paper No. 5), please amend the above-identified U.S. patent application as follows:

In the Claims

Please cancel claims 3, 9, 11, 12, 13 and 14 without prejudice to their reentry at some later date.

Please amend the claims as follows:

1. (Amended) A method of filling an opening in an oxide layer, over a liner layer formed on a surface of a silicide substrate underlying both the oxide layer and the liner layer, comprising:

forming a first continuous layer comprising silicon, by either physical vapor deposition (PVD) or chemical vapor deposition (CVD) at a first temperature in the range 500°C to 650°C on the oxide layer and on the liner layer; and

forming a second layer, comprising a refractory material, on the first layer at a second temperature that is lower than the first temperature so as to cover the same and to also substantially fill the opening.

AI
SUB
BI